SHEET 1 OF 1

INIEC		י חופרו ר	ATTORNEY'S DKT NO. 025219-382		APPLICATION NO. Unassigned				
INFORMATION DISCLOSURE CITATION				APPLICANT Bernard Aspar, e	APPLICANT Bernard Aspar, et al.				
				FILING DATE	FILING DATE GROUP				
	PTO-1		Herewith						
	T-	<u>U</u>	J.S. PATENT DO	OCUMENTS		т	T		
EXAMINER'S INITIALS	PATENT NO.	DATE	<u> </u>	NAME	CLASS	SUBCLASS	FILING	G DATE	
101	5,256,581	10/26/93	Foerstner, et.	. al.	437	24	<u> </u>		
201	5,374,564	12/20/94	Bruel		437	24	5		
1000	5,783,477	07/21/98	Kish, Jr. et. a	al.	438	455	8. 99.		
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₩~	Hiroshi Wada, et al.: "Electrical Characteristics Of Directly-Bonded GaAs and InP" Applied Physics Letters, vol. 62, no. 7, 15 February 1993, pages 738-740, XP000338292								
									
									
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EXAMINER	1000		D/	ATE CONSIDERED)				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance <u>and</u> not considered. Include copy of this form with next communication to applicant.